

Catalyst.

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TITLE: TREATMENT OF EXHAUST GAS IN PRODUCING SEMICONDUCTOR

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ABSTRACT:

PURPOSE: To efficiently treat an exhaust gas, by allowing the exhaust gas in production of semiconductor to cause catalytic reaction with metallic catalyst, forming a compd. on the catalyst, recovering and removing as the metallic compd.

CONSTITUTION: The exhaust gas contg. AsH<SB>3</SB>, PH<SB>3</SB>, B<SB>2</SB>H<SB>6</SB>, SiH<SB>4</SB>, Ga, Ge, P, and In etc., which is generated in the production of semiconductor by the CVD process, etc., is allowed to cause catalytic reaction with the metallic catalyst such as Pt, CuO, CrO or MnO<SB>2</SB>-Al<SB>2</SB>O<SB>3</SB> at 200~300°C, and then the compd. such as SiO<SB>2</SB> is formed on the catalyst. The formed metallic compd. is recovered as the rare metal component. Thus, the gas in the

production of semiconductor is efficiently treated.

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